

## **INCHANGE SEMICONDUCTOR**

# **Isc N-Channel MOSFET Transistor**

## IRFU220N

## FEATURES

- With TO-251(IPAK) packaging
- Uninterruptible power supply
- · High speed switching
- · Hard switched and high frequency circuits
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

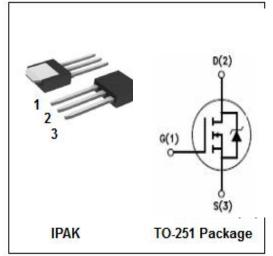
#### APPLICATIONS

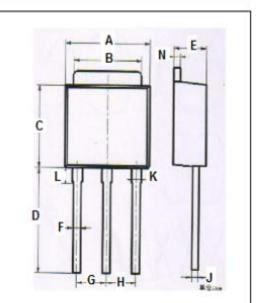
- Switching applications
- DC-DC converters
- High frequency

SYMBOL	PARAMETER	VALUE	UNIT			
V <sub>DSS</sub>	Drain-Source Voltage	200	V			
V <sub>GSS</sub>	Gate-Source Voltage	±20	V			
ID	Drain Current-Continuous@Tc=25 $^{\circ}$ CTc=100 $^{\circ}$ C	5.0 3.5	А			
I <sub>DM</sub>	Drain Current-Single Pulsed	20	A			
PD	Total Dissipation	43	W			
Tj	Operating Junction Temperature	-55~175	°C			
T <sub>stg</sub>	Storage Temperature	-55~175	°C			

THERMAL CHARACTERISTICS						
SYMBOL	PARAMETER	МАХ	UNIT			
Rth(ch-c)	Channel-to-case thermal resistance	1.05	°C <b>/W</b>			
Rth(ch-a)	Channel-to-ambient thermal resistance	110	°C/W			

1





	mm		
DIM	MIN	MAX	
Α	6.40	6.48	
В	5.10	5.50	
С	5.80	6.20	
D	9.20	9.60	
E	2.20	2.40	
F	0.50	0.70	
G	2.09	2.49	
H	2.09	2.49	
J	0.40	0.60	
Κ	0.70	0.90	
L	1.60	2.00	
Ν	0.40	0.60	

#### isc website: www.iscsemi.cn

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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA	200			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =±20V; I <sub>D</sub> =0.25mA	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> =2.9A			600	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V			±0.1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =200V; V <sub>GS</sub> = 0V@Tc=25℃ Tc=125℃			25 250	μ Α
V <sub>SDF</sub>	Diode forward voltage	I <sub>SD</sub> =2.9A, V <sub>GS</sub> = 0 V			1.3	V

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2